

Abstract of the Disclosure

An (SiGe)C layer having a stoichiometric ratio of about 1:1 is locally formed on an Si layer, a large forbidden band width semiconductor device is prepared inside the layered structure thereof and an Si semiconductor integrated circuit is formed in the regions not formed with the layered structure, whereby high frequency high power operation of the device is enabled by the large forbidden band width semiconductor device and high performance is attained by hybridization of the Si integrated circuit.